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(54) **VERTICAL CHANNEL THIN FILM TRANSISTOR AND METHOD FOR MANUFACTURING THE SAME**

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ABSTRACT

Provided is a method for manufacturing a vertical channel thin film transistor. The method for manufacturing the vertical channel thin film transistor includes forming a bottom source drain electrode, forming a first interlayer insulating layer, forming first middle source drain electrodes, forming a second interlayer insulating layer, forming a top source drain electrode, forming an opening through which portions of the bottom source drain electrode, the first middle source drain electrodes, and the top source drain electrode are exposed, forming channel layers, forming a gate insulating layer on the channel layers, the bottom source drain electrode, the first middle source drain electrodes, and the top source drain electrode, and forming gate electrodes on the gate insulating layer.

